Title (en)

PLANAR MOSFET WITH TEXTURED CHANNEL AND GATE

Title (de)

PLANARES MOSFET MIT TEXTURIERTEM KANAL UND GATE

Title (fr)

TRANSISTOR À EFFET DE CHAMP SEMI-CONDUCTEUR À OXYDE MÉTALLIQUE (MOSFET) PLAN AVEC CANAL TEXTURÉ ET GÂCHETTE

Publication

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Application

EP 10834973 A 20101124

Priority

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Abstract (en)

[origin: WO2011068737A2] A semiconductor device is disclosed that includes a semiconductor substrate having a channel region and respective source and drain regions formed on opposite sides of the channel region. The channel region includes at least one pore. A gate is formed on the semiconductor substrate between the source and drain regions and includes at least one pin received by respective ones of the at least one pore. A dielectric layer is disposed between the gate and the semiconductor substrate.

IPC 8 full level

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CPC (source: EP US)

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